

Amendments to the Claims

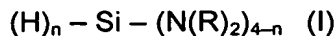
This listing of claims will replace the originally filed claims in the application.

Listing of Claims:

Claims 1 – 10 (cancelled)

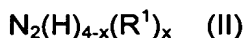
Claim 11 (new): A method for producing silicon nitride film by chemical vapor deposition, characterized by

feeding gaseous aminosilane with formula (I)



(each R is independently selected from the hydrogen atom, C₁₋₄ alkyl, and the trimethylsilyl group and n is an integer with a value of about 0-3, wherein the groups R are not all simultaneously a hydrogen atom)

and gaseous hydrazine compound with formula (II)



(each R¹ is independently selected from methyl, ethyl, and phenyl and x is an integer with a value of about 0-4)

into a chemical vapor deposition reaction chamber that holds at least one substrate, and

forming silicon nitride film on said at least one substrate by reacting the two gases in the chemical vapor deposition reaction chamber.

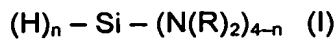
Claim 12 (new): The method of claim 11, wherein the reaction is run at temperatures of about 300°C to about 650°C.

Claim 13 (new): The method of claim 11, wherein the pressure in the reaction chamber is established at about 0.1-1000 torr.

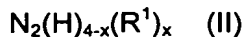
Claim 14 (new): The method of claim 11, wherein the aminosilane: hydrazine compound molar ratio is about 1:1 to about 1:100.

Claim 15 (new): A method for producing silicon oxynitride film by chemical vapor deposition, characterized by

feeding gaseous aminosilane with formula (I)



(each R is independently selected from the hydrogen atom, C₁₋₄ alkyl, and the trimethylsilyl group and n is an integer with a value of about 0-3, wherein the groups R are not all simultaneously a hydrogen atom),
gaseous hydrazine compound with formula (II)



(each R¹ is independently selected from methyl, ethyl, and phenyl and x is an integer with a value of about 0-4), and oxygenated gas
into a chemical vapor deposition reaction chamber that holds at least one substrate, and
forming silicon oxynitride film on said at least one substrate by reacting these gases in the chemical vapor deposition reaction chamber.

Claim 16 (new): The method of claim 15 for producing silicon oxynitride film, wherein the oxygenated gas is at least one selection from the group consisting of O₂, O₃, H₂O, H₂O₂, NO, NO₂, and N₂O.

Claim 17 (new): The method of claim 15, wherein the reaction is run at temperatures of about 300°C to about 650°C.

Claim 18 (new): The method of claim 15, wherein the pressure in the reaction chamber is established at about 0.1-1000 torr.

Claim 19 (new): The method of claim 15, wherein the aminosilane:hydrazine compound molar ratio is about 1:1 to about 1:100.

Claim 20 (new): The method of claim 15, wherein the aminosilane:oxygenated gas molar ratio is about 1:1 to about 1:100.